

isc Silicon NPN Power Transistor

BU222A

DESCRIPTION

- · High Collector-Base Breakdown Voltage-
 - : V_{(BR)CBO}= 525V (Min)
- High Current Capability
- · High Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

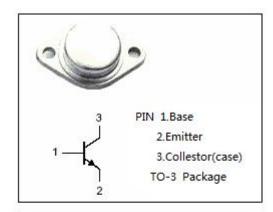
APPLICATIONS

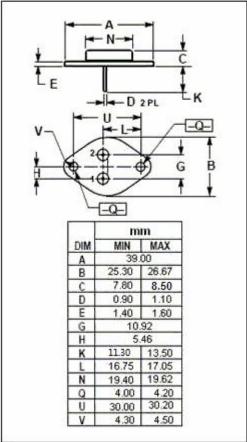




ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT	
V _{CBO}	Collector-Base Voltage	525	V	
V _{CEO}	Collector-Emitter Voltage	475	V	
V _{EBO}	Emitter-Base Voltage 8		V	
lc	Collector Current-Continuous	6	Α	
I _B	Base Current-Continuous	2	Α	
P _C	Collector Power Dissipation @T _C =25°C	75	W	
Tj	Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature Range	-65~150	$^{\circ}$	







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	475			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	525			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 0.1mA ; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 525V; I _E =0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C =0			0.1	mA
h _{FE-1}	DC Current Gain	I _C = 3A; V _{CE} = 4V	10			
h _{FE-2}	DC Current Gain	I _C = 6A; V _{CE} = 4V	3			
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A;V _{CE} = 10V;f _{test} = 1MHz	10			MHz

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